

Electronics and Communication Department

GLA University, Mathura

Topic wise Syllabus for Electronics Engineering BECG 0001 For End Term

1. Operational Amplifier
 - Circuit symbol of Op-Amp
 - Ideal Characteristics of Op-Amp
 - Application of Operational Amplifier (Op-Amp)
 - Circuit diagram and derivation of output voltage expression for Inverting Operational Amplifier (Op-Amp).
 - Circuit diagram and derivation of output voltage expression for Non-Inverting Operational Amplifier (Op-Amp).
 - Circuit diagram and derivation of output voltage expression for Operational Amplifier (Op-Amp) as Adder.
 - Circuit diagram and derivation of output voltage expression for Operational Amplifier (Op-Amp) as Integrator.
 - Circuit diagram and derivation of output voltage expression for Operational Amplifier (Op-Amp) as Differentiator.
 - Numerical on Adder, Inverting OP-Amp, Non Inverting Op-Amp
2. Digital Electronics
 - Minimization (simplification) of logic expression using K-Map
 - 4 Variable K-Map with don't care and without don't care.
 - 3 Variable K-Map with don't care and without don't care.
 - 1's and 2's complement.
 - Subtraction using 2's complement.
 - Conversion of Logic expression into Canonical SOP and Canonical POS (find minterm and maxterm for given expression).
 - Minimization (simplification) of logic expression using Boolean Algebra.
 - Circuit symbol and truth table for logic gates
 - Basic Gates: AND Gate , OR Gate, Not Gate
 - Universal Gates: NAND Gate, NOR Gate
 - Derived Gates: Ex-Or Gate, Ex-Nor Gate.
 - Design/Implement Basic Gates (i.e AND Gate, OR Gate, NOT Gate) using NOR Gate only.
 - Design/Implement Basic Gates (i.e AND Gate, OR Gate, NOT Gate) using NAND Gate only.
 - Binary addition and Subtraction.
 - Number System: conversion from one base to another Base.
3. Bipolar Junction Transistor
 - Input and Output Characteristics of BJT in Common Base Configuration (CB).
 - Input and Output Characteristics of BJT in Common Emitter Configuration (CE).
 - Comparison between CB, CE and CC configuration.
 - Working of NPN Bipolar junction Transistor.
 - Numerical on I_C , I_B , I_E , α , and β
4. Numerical on Bias Stabilization.
 - Voltage Divider / Potential Divider Bias Stabilization
 - Emitter Bias stabilization
 - Fixed Bias stabilization

5. Stability Factor
 - Definition and formula of Stability factor.
 - Derive Expression of Stability factor for BJT in common emitter configuration.
6. Field Effect Transistor
 - Comparison between BJT and FET

***** Revision of MID term Syllabus*****

1. Breakdown Mechanism.
 - Comparison between Zener breakdown and Avalanche Breakdown.
2. Clamper
3. V-I characteristics of p-n diode
4. Diode Resistance
 - Dynamic resistance (theory).
 - Static Resistance (theory).
5. Diode Capacitance
 - Transition /Depletion capacitance (theory).
 - Diffusion Capacitance (theory).
6. Rectifier
 - Circuit and working of Half wave rectifier.
 - Circuit and working of Bridge rectifier.
 - Numerical on rectifier (attempt question of tutorial sheet Q1 - Q5,Q5).

Prepared BY:
SWETA
(Assistant Professor)
Electronics and Communication Department